



#### 20V N-Channel Enhancement Mode MOSFET

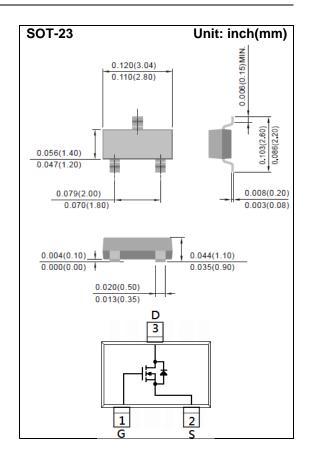
Voltage 20 V Current 4.1A

#### **Features**

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@4.1A<56mΩ</li>
- $R_{DS(ON)}$ ,  $V_{GS}@2.5V$ ,  $I_D@2.8A<68m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@1.8V, I<sub>D</sub>@1.5A<95mΩ</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case: SOT-23 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0084 grams



## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER  |                      | SYMBOL          | LIMIT       | UNITS |  |
|--|----------------------|-----------------|-------------|-------|--|
| Drain-Source Voltage                             |                      | V <sub>DS</sub> | 20          | V     |  |
| Gate-Source Voltage                              |                      | $V_{GS}$        | <u>+</u> 12 |       |  |
| Continuous Drain Current                         |                      | I <sub>D</sub>  | 4.1         | A     |  |
| Pulsed Drain Current                             |                      | I <sub>DM</sub> | 16.4        |       |  |
| Power Dissipation                                | T <sub>a</sub> =25°C | P <sub>D</sub>  | 1.25        | W     |  |
|  | Derate above 25°C    |                 | 10          | mW/°C |  |
| Operating Junction and Storage Temperature Range |                      | $T_J, T_{STG}$  | -55~150     | °C    |  |
| Typical Thermal Resistance                       |                      |                 |             |       |  |
| - Junction to Ambient (Note 3)                   |                      | $R_{\theta JA}$ | 100         | °C/W  |  |

June 30,2017-REV.01 Page 1





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION  | MIN. | TYP. | MAX.         | UNITS |  |
|----------------------------------|---------------------|---|------|------|--------------|-------|--|
| Static                           |                     |   |      |      |              |       |  |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA                                      | 20   | -    | -            | V     |  |
| Gate Threshold Voltage           | $V_{GS(th)}$        | $V_{DS}=V_{GS}$ , $I_{D}=250uA$   | 0.4  | 0.66 | 1.2          |       |  |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.1A                                     | -    | 41   | 56           | mΩ    |  |
|                                  |                     | V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.8A                                     | -    | 50   | 68           |       |  |
|                                  |                     | V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.5A                                     | -    | 66   | 95           |       |  |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V                                       | -    | -    | 1            | uA    |  |
| Gate-Source Leakage Current      | $I_{GSS}$           | V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V                             | -    | -    | <u>+</u> 100 | nA    |  |
| Dynamic (Note 5)                 |                     |   |      |      |              |       |  |
| Total Gate Charge                | $Q_g$               | V <sub>DS</sub> =10V, I <sub>D</sub> =4.1A,<br>V <sub>GS</sub> =4.5V (Note 1,2) | -    | 4.6  | -            | nC    |  |
| Gate-Source Charge               | $Q_gs$              |   | -    | 0.8  | -            |       |  |
| Gate-Drain Charge                | $Q_gd$              |   | -    | 1    | -            |       |  |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,                                      | -    | 350  | -            | pF    |  |
| Output Capacitance               | Coss                |   | -    | 40   | -            |       |  |
| Reverse Transfer Capacitance     | Crss                | f=1.0MHZ  | -    | 29   | -            |       |  |
| Turn-On Delay Time               | td <sub>(on)</sub>  | V 40V L 44A   | -    | 4    | -            |       |  |
| Turn-On Rise Time                | tr                  | $V_{DD}$ =10V, $I_{D}$ =4.1A, $V_{GS}$ =4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)    | -    | 47   | -            | ns    |  |
| Turn-Off Delay Time              | td <sub>(off)</sub> |   | -    | 18   | -            |       |  |
| Turn-Off Fall Time               | tf                  |   | -    | 10   | -            |       |  |
| Drain-Source Diode               |                     |   |      |      |              |       |  |
| Maximum Continuous Drain-Source  | -                   |   |      |      | 4.5          | А     |  |
| Diode Forward Current            | I <sub>S</sub>      |   | _    | -    | 1.5          |       |  |
| Diode Forward Voltage            | $V_{SD}$            | I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V                                       | -    | 0.75 | 1.2          | V     |  |

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<a>2%</a>.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

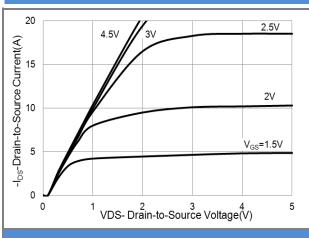


Fig.1 On-Region Characteristics

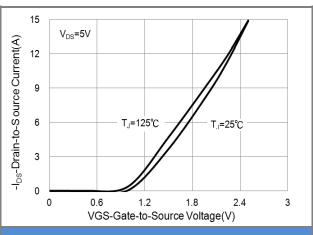


Fig.2 Transfer Characteristics

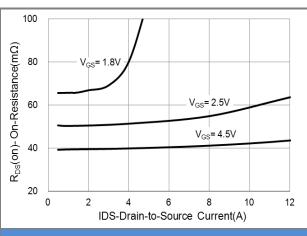


Fig.3 On-Resistance vs. Drain Current

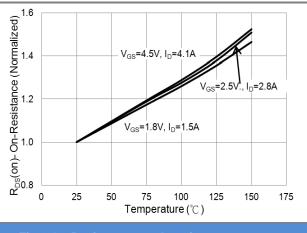


Fig.4 On-Resistance vs. Junction temperature

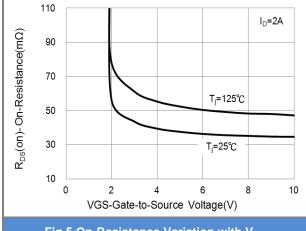
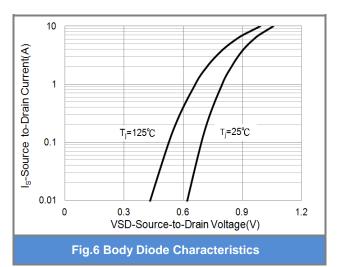


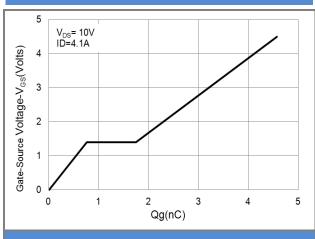
Fig.5 On-Resistance Variation with V<sub>GS</sub>







#### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

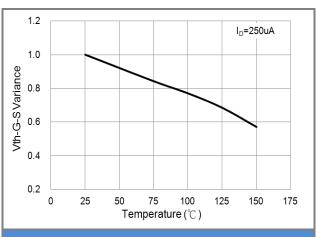


Fig.8 Threshold Voltage Variation with Temperature

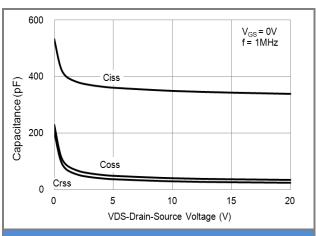


Fig.9 Capacitance vs. Drain-Source Voltage

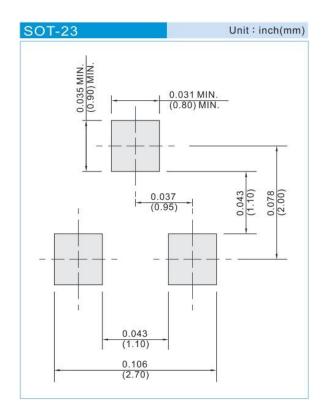




### **Part No Packing Code Version**

| Part No Packing Code | Package Type | Packing Type     | Marking | Version      |
|----------------------|--------------|------------------|---------|--------------|
| PJA3412-AU_R1_000A1  | SOT-23       | 3K pcs / 7" reel | A12     | Halogen free |

### **Mounting Pad Layout**







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